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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
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2292	7590	03/13/2007		
BIRCH STEWART KOLASCH & BIRCH			EXAMINER	
PO BOX 747			RUDE, TIMOTHY L	
FALLS CHURCH, VA 22040-0747				
			ART UNIT	PAPER NUMBER
			2871	

SHORTENED STATUTORY PERIOD OF RESPONSE	NOTIFICATION DATE	DELIVERY MODE
3 MONTHS	03/13/2007	ELECTRONIC

Please find below and/or attached an Office communication concerning this application or proceeding.

If NO period for reply is specified above, the maximum statutory period will apply and will expire 6 MONTHS from the mailing date of this communication.

Notice of this Office communication was sent electronically on the above-indicated "Notification Date" and has a shortened statutory period for reply of 3 MONTHS from 03/13/2007.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

mailroom@bskb.com

Office Action Summary	Application No.		Applicant(s)	
	10/028,305		SUNG CHAE ET AL.	
	Examiner		Art Unit	
	Timothy L. Rude		2871	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 09 November 2006.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-15,21 and 22 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-15,21 and 22 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- | | |
|--|---|
| 1) <input type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413) |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | Paper No(s)/Mail Date. _____ |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO/SB/08) | 5) <input type="checkbox"/> Notice of Informal Patent Application |
| Paper No(s)/Mail Date _____ | 6) <input type="checkbox"/> Other: _____ |

DETAILED ACTION

Continued Examination Under 37 CFR 1.114

A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 12 September 2006 has been entered.

Claims

1. Claims 1, 8, and 21 are amended.

Claim Objections

2. Claims 1, 8, and 21 are objected to because of the following informalities:

Newly added limitations attribute "defining a separation region" to a second semiconductor layer over the first semiconductor layer while a redundant "to define the separation region" is attributed to an alignment of the first metal layer and the second semiconductor layer. Considering all reasonable definitions for "defining" and for "to define", examiner feels these are contradictory limitations. Examiner asserts that the given structure (separation region) can be defined by only one set of limitations. For examination purposes, examiner will consider the prior limitations remain unchanged,

i.e., the separation region is defined by the defined outer edge of first metal layer being lined up with the defined outer edge of the second semiconductor layer.

Appropriate correction is required.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

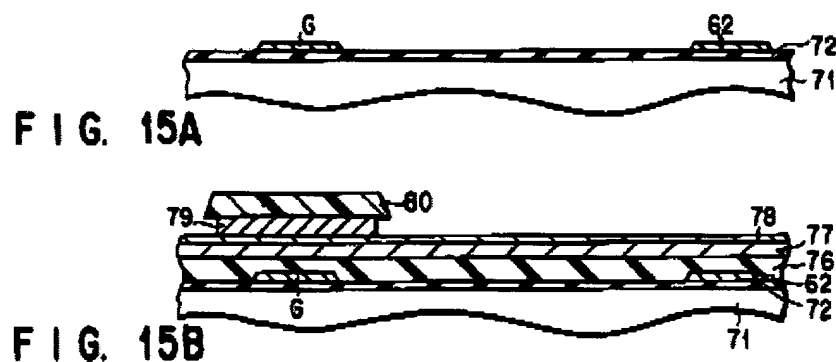
3. Claims 1, 8, 21, and 22 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ueda et al (Ueda) USPAT 6,078,365 in view of Hibino et al (Hibino) 6,529,251 B2.

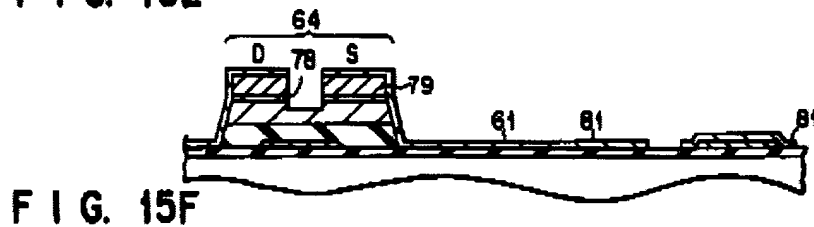
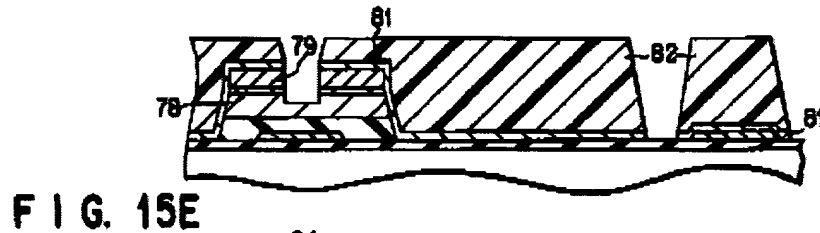
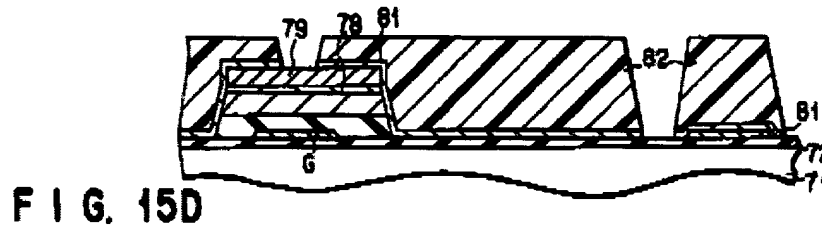
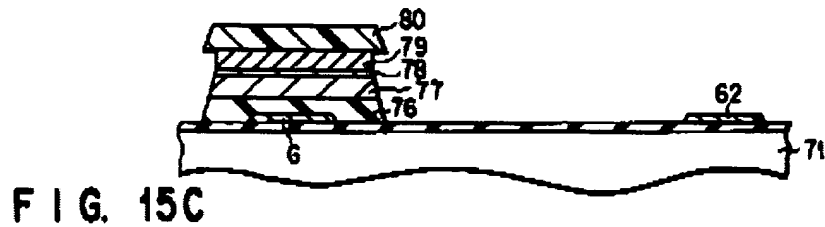
As to claims 1, 8, 21, and 22, Ueda discloses a device and a method of making said device in an embodiment in Figures 15A-15F (col. 12, line 58, through col. 18, line 33, especially col. 16, line 64, through col. 18, line 33) comprising: a substrate, 71; a gate electrode, G, over the substrate; a first semiconductor layer, 77, over the gate electrode; a second semiconductor layer, 78, over the first semiconductor layer and having a defined outer edge, source, S, and drain, D, electrodes (Applicant's first metal layer) on the second semiconductor layer, the first metal layer patterned in a same pattern as the second semiconductor layer such that the first metal layer and second semiconductor layer define the channel (Applicant's separation region). Please note that this is by way of only one photolithography pattern per Figures (Applicant's patterned in the same pattern).

Ueda further discloses the use of source, S, and drain, D, comprised of Aluminum and Molybdenum disposed on Molybdenum (Mo/Al/Mo) (comprises Applicant's electrodes over the first metal layer), the source and drain electrodes patterned the same as the first metal layer and having a defined outer edge and the second semiconductor layer (col. 17, lines 22-42) define first upper portion of the separation region, and the source and drain electrodes include a second (Al) and a third

(Mo) metal layer, in order to use a low resistance metal such as Aluminum for improved conductivity of the circuit components (col. 17, line 55, through col. 18, line 5).

The outer defined edges of the metal layers and silicon layers are all lined up and abut each other to define the channel as illustrated.





Ueda discloses (col. 12, line 58, through col. 18, line 33, especially col. 16, line 64, through col. 18, line 33) the method of forming a liquid crystal display device, comprising: forming a gate electrode on a substrate; forming an active layer over the gate electrode; forming a first semiconductor layer over the active layer; forming a second semiconductor layer over the first semiconductor layer; forming a first metal layer over the second semiconductor layer; patterning the first metal layer and the second semiconductor layer in a same pattern; and forming a source electrode and a drain electrode over the first metal layer.

The outer defined edges of the metal layers and silicon layers are all lined up and abut each other to define the channel as illustrated.

Ueda does not explicitly disclose the newly added limitations as to wet etching followed by dry etching.

Hibino teaches the use of a method including the steps of wet etching followed by dry etching [col. 13, lines 28-65] to reduce defects [col. 4, lines 21-30] and improve uniformity of TFT properties [col. 14, lines 1-10]. Please note that this would preclude unwanted TFT defects (non-uniform TFTs) which include defective TFTs with unwanted high leakage current. Also, the combination of Hibino to Ueda matches Applicant's structure and therefore must match Applicant's newly added performance limitation as to "and thereby reduce leakage current".

Hibino is evidence that workers of ordinary skill in the art would find the reason, suggestion, or motivation to add the steps of wet etching followed by dry etching to reduce defects and improve uniformity of TFT properties.

Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the invention of Ueda with the steps of wet etching followed by dry etching of Hibino to reduce defects and improve uniformity of TFT properties.

4. Claims 1-15 and 21-22 are rejected under 35 U.S.C. 103(a) as being unpatentable over Applicant's admitted prior art (APA) in view of Ueda and further in view of Hibino.

As to claims 1, 8, and 21-22, APA discloses a conventional liquid crystal display device and the method of making said device in Figures 1-5 and Specification pages 1-5, comprising: a substrate, 1; a gate electrode, 3, over the substrate; a first semiconductor layer, 15, over the gate electrode; a second semiconductor layer, 17, over the first semiconductor layer, source, 5, and drain, 7, electrodes (Applicant's first metal layer) on the second semiconductor layer, the first metal layer patterned in a same pattern as the second semiconductor layer such that the first metal layer and second semiconductor layer define the channel, 30 (Applicant's separation region) per Figure 3C (specification page 3, lines 28-31). Please note that this is well known in the art to take only one photolithography pattern (Applicant's patterned in the same pattern).

APA does not explicitly disclose (1) source and drain electrodes over the first metal layer, the source and drain electrodes patterned the same as the first metal layer and the second semiconductor layer define first upper portion of the separation region, and the source and drain electrodes include a second and a third metal layer, and (2) wet etching followed by dry etching.

Ueda teaches (1) an embodiment in Figures 15A-15F (col. 12, line 58, through col. 18, line 33, especially col. 16, line 64, through col. 18, line 33) the use of source, S, and drain, D, comprised of Aluminum and Molybdenum disposed on Molybdenum

(Mo/Al/Mo) (comprises Applicant's electrodes over the first metal layer), the source and drain electrodes patterned the same as the first metal layer and the second semiconductor layer (col. 17, lines 22-42) define first upper portion of the separation region, and the source and drain electrodes include a second (Al) and a third (Mo) metal layer, in order to use a low resistance metal such as Aluminum for improved conductivity of the circuit components (col. 17, line 55, through col. 18, line 5).

Ueda is evidence that ordinary workers in the art of liquid crystals would find the reason, suggestion, or motivation to add source and drain electrodes over the first metal layer, the source and drain electrodes patterned the same as the first metal layer and the second semiconductor layer define first upper portion of the separation region, and the source and drain electrodes include a second and a third metal layer in order to use a low resistance metal such as Aluminum for improved conductivity of the circuit components.

Therefore, it would have been obvious to one having ordinary skill in the art of liquid crystals at the time the invention was made to modify the LCD of APA with added source and drain electrodes over the first metal layer, the source and drain electrodes patterned the same as the first metal layer and the second semiconductor layer define first upper portion of the separation region, and the source and drain electrodes include a second and a third metal layer in order to use a low resistance metal such as Aluminum for improved conductivity of the circuit components.

Hibino teaches (2) the use of a method including the steps of wet etching followed by dry etching [col. 13, lines 28-65] to reduce defects [col. 4, lines 21-30] and

improve uniformity of TFT properties [col. 14, lines 1-10]. Please note that this would preclude unwanted TFT defects (non-uniform TFTs) which include defective TFTs with unwanted high leakage current. Also, the combination of Hibino to Ueda matches Applicant's structure and therefore must match Applicant's newly added performance limitation as to "and thereby reduce leakage current". Hibino teaches, regarding his method being thus described, it will be obvious that the same may be varied in many ways. Such variations are not to be regarded as a departure from the spirit and scope of the invention, and all such modifications as would be obvious to one skilled in the art [col. 14, lines 8-14].

Hibino is evidence that workers of ordinary skill in the art would find the reason, suggestion, or motivation to add the steps of wet etching followed by dry etching to reduce defects and improve uniformity of TFT properties.

Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the invention of APA in view of Ueda with the steps of wet etching followed by dry etching of Hibino to reduce defects and improve uniformity of TFT properties.

As to claim 2, APA discloses a device, further comprising: an insulating layer in between the gate electrode and the first semiconductor layer; a protective layer, 21, over the source and drain electrodes and defining a second upper portion of the separation region (Figure 3D) and a contact hole, 19b, exposing a portion of the drain electrode; and a pixel electrode, 23, in the contact hole (Figure 3E).

As to claim 3, APA in view of Ueda and Hibino, as combined above, discloses the device of claim 1 above, wherein; the second metal layer includes aluminum (Al, Ueda, col. 17, lines 22-30).

As to claim 4, APA in view of Ueda and Hibino, as combined above, discloses the device of claim 1 above, wherein the first and third metal layers are formed of the same material (Mo, Ueda, col. 17, lines 22-30).

As to claim 5, APA in view of Ueda and Hibino, as combined above, discloses the device of claim 1 above.

The device of claim 1 above does not explicitly disclose a device wherein the first and third metal layers are formed of different materials.

Ueda teaches the use of a refractory metal of Cr or a Mo-Ta alloy (col. 12, lines 62-67) as art recognized equivalents suitable for the intended purpose of forming an undercoat conductive layer (MPEP 2144.07).

Ueda is evidence that ordinary workers in the art of liquid crystals would find the reason, suggestion, or motivation to use Cr or a Mo-Ta alloy for one of the first or third metal layers, resulting in the claimed device wherein the first and third metal layers are formed of different materials.

Therefore, it would have been obvious to one having ordinary skill in the art of liquid crystals at the time the invention was made to modify the LCD of APA in view of

Ueda with the Cr or a Mo-Ta alloy for one of the first or third metal layers, resulting in the claimed device wherein the first and third metal layers are formed of different materials.

As to claim 6, APA in view of Ueda and Hibino, as combined above, discloses the device of claim 1 above, wherein the first and third metal layers include molybdenum (Mo, Ueda, col. 17, lines 22-30).

As to claim 7, APA in view of Ueda and Hibino, as combined above, discloses the device of claim 4 above, wherein the first and third metal layers are formed include molybdenum (Mo, Ueda, col. 17, lines 22-30).

As to claim 9, the method of claim 8, wherein forming the source and drain electrodes includes forming a second metal layer over the first metal layer, forming a third metal layer over the first metal layer, and patterning the second and third metal layers in the same pattern as the first metal layer and second semiconductor layer in the channel region so that a channel portion of the first semiconductor layer is exposed, would have been obvious given the device structure above.

As to claim 10, APA in view of Ueda and Hibino, as combined above, discloses the method of claim 8 above, wherein the first and third metal layers include molybdenum (Mo, Ueda, col. 17, lines 22-30).

As to claim 11, APA in view of Ueda and Hibino, as combined above, discloses the method of claim 9 above, wherein the first and third metal layers are formed of the same material (Mo, Ueda, col. 17, lines 22-30).

As to claim 12, APA in view of Ueda and Hibino, as combined above, discloses the method of claim 9 above.

The method of claim 9 above does not explicitly disclose a device wherein the first and third metal layers are formed of different materials.

Ueda teaches the use of a refractory metal of Cr or a Mo-Ta alloy (col. 12, lines 62-67) as art recognized equivalents suitable for the intended purpose of forming an undercoat conductive layer (MPEP 2144.07).

Ueda is evidence that ordinary workers in the art of liquid crystals would find the reason, suggestion, or motivation to use Cr or a Mo-Ta alloy for one of the first or third metal layers, resulting in the claimed method wherein the first and third metal layers are formed of different materials.

Therefore, it would have been obvious to one having ordinary skill in the art of liquid crystals at the time the invention was made to modify the LCD of APA in view of Ueda with the Cr or a Mo-Ta alloy for one of the first or third metal layers, resulting in the claimed method wherein the first and third metal layers are formed of different materials.

As to claim 13, APA in view of Ueda Hibino, as combined above, discloses the method of claim 9 above, wherein; the second metal layer includes aluminum (Al, Ueda, col. 17, lines 22-30).

As to claim 14, APA in view of Ueda and Hibino, as combined above, discloses the method of claim 9 above, wherein the first and third metal layers include molybdenum (Mo, Ueda, col. 17, lines 22-30).

As to claim 15, APA in view of Ueda and Hibino, as combined above, discloses the method of claim 8 above, wherein the patterning of the first metal layer and second semiconductor layer define channel region includes removing a portion of the first metal layer and second metal layer corresponding to the gate electrode and exposing the first semiconductor layer (Figure 15F, and col. 17, lines 14-67).

Response to Arguments

Applicant's arguments filed on 12 September 2006 and 09 November 2006 have been fully considered but they are not persuasive.

Applicant's ONLY substantive arguments are as follows:

(1) Regarding base claims 8 and 21, the applied prior art does not disclose the newly added limitations.

(2) Regarding base claims 8 and 21, there is no motivation to combine because Ueda does not have a structure that requires the improvement of the teaching of Hibino.

(3) Regarding base claims 8 and 21, there is no motivation to combine because the structure of Ueda has a layer that Hibino does not have.

(4) Regarding base claims 8 and 21, there is no motivation to combine because there is improper hindsight.

(5) Regarding base claims 8 and 21, there is no motivation to combine because Ueda's structure is substantially different from Hibino.

(6) Regarding base claims 8 and 21, there is no motivation to combine because Hibino does not disclose use of its source electrodes as masks.

(7) Regarding base claims 8 and 21, there is no motivation to combine because Hibino teaches a two-layer structure rather than a three-layer structure.

(8) Regarding base claims 8 and 21, there is no motivation to combine because the two references differ significantly in ways Applicant numbers 1-4 on page 12 of 21.

(9) Regarding base claims 8 and 21, there is no motivation to combine because examiner has not established that the problems exist in Ueda.

(10) Regarding base claims 8 and 21, there is no motivation to combine because of broad-brush basis.

(11) Applicant argues insufficient response to arguments in Final Rejection and Advisory Action.

(12) Applicant repeats arguments regarding Admitted Prior Art.

(13) Applicant argues alignment of layers is not addressed.

(14) Dependent claims are allowable because they directly or indirectly depend from an allowable base claim.

Examiner's responses to Applicant's ONLY arguments are as follows:

(1) It is respectfully pointed out that newly added limitations are addressed in the rejections above.

(2) It is respectfully pointed out that Ueda has the electrode structure of Applicant's device which needs the improvement of the method of Hibino. It is also respectfully pointed out that primary references virtually never anticipate the need for the improvement taught by the secondary reference; nothing is perfect, anything can be improved upon.

(3) It is respectfully pointed out that Hibino is a robust teaching of how and why one would want to use both wet and dry etching to obtain desired etching of some layers without over etching other layers. With the teaching of Hibino, it would be obvious to use dry etching to etch back the layers in such a way as to result in no unwanted electrical shorting between non-adjacent layers.

(4) It is respectfully pointed out that Hibino provides robust motivation that is applicable to Ueda. No improper hindsight was used.

(5) It is respectfully pointed out that the method of Hibino, with proper motivation to combine, is applicable to a wide variety of structures and materials [col. 14, lines 1-14, and col. 13, line 17-67].

(6) It is respectfully pointed out that the source electrodes of Hibino are covering the layers below and therefore inherently mask the underlying layers.

(7) It is respectfully pointed out that the method of Hibino, with proper motivation to combine, is applicable to a wide variety of structures, layer counts, and materials [col. 14, lines 1-14, and col. 13, line 17-67].

(8) It is respectfully pointed out that the method of Hibino, with proper motivation to combine, is applicable to a wide variety of structures, layer counts, and materials [col. 14, lines 1-14, and col. 13, line 17-67]. In fact, the method of Hibino would be applicable to many structures beyond TFTs for LCDs. Hibino is a very broad teaching as to the artful use of both dry and wet etching to obtain desired etching of some layers without over etching other layers. With the teaching of Hibino, it would be obvious to use dry etching to etch back the layers in such a way as to result in no unwanted electrical shorting between non-adjacent layers in any of a wide variety of structures.

(9) It is respectfully pointed out that Ueda has the electrode structure of Applicant's device which needs the improvement of the method of Hibino. It is also respectfully pointed out that primary references virtually never anticipate the need for the improvement taught by the secondary reference; nothing is perfect, anything can be improved upon.

(10) It is respectfully pointed out that Ueda has the electrode structure of Applicant's device which needs the improvement of the method of Hibino. It is also respectfully pointed out that primary references virtually never anticipate the need for the improvement taught by the secondary reference; nothing is perfect, anything can be

improved upon. The method of Hibino, with proper motivation to combine, is applicable to a wide variety of structures, layer counts, and materials [col. 14, lines 1-14, and col. 13, line 17-67]. In fact, the method of Hibino would be applicable to many structures beyond TFTs for LCDs. Hibino is a very broad teaching as to the artful use of both dry and wet etching to obtain desired etching of some layers without over etching other layers. With the teaching of Hibino, it would be obvious to use dry etching to etch back the layers in such a way as to result in no unwanted electrical shorting between non-adjacent layers in any of a wide variety of structures.

(11) It is respectfully pointed out that arguments of the Final Rejection were moot because the claims were substantially amended. The fact that the claims remained rejected on the same grounds is not at issue. The Advisory Action addressed Applicant's arguments robustly while prosecution was closed (After Final).

(12) It is respectfully pointed out that MPEP 608.01(c) (2) clearly indicates that the content of the Background of the Invention section is to provide a description of the related art that describes to the extent practical the state of the prior art or other information disclosed. Where applicable, the problems involved in the prior art or other information disclosed which are solved by the Applicant's invention should be indicated. Applicant's own reference in the Background of the Invention to Figures 1-5 as being of a "conventional" device (Specification Pages 1-5) with Figures 1-5 "conventional" are consistent with requirement of MPEP 608.01(c) (2) to disclose such prior art, and the drawing labels should so reflect per MPEP 608.02(g). Please see also MPEP 707.05(b) which states that MPEP 609 sets forth the positive guidelines for Applicants, their

Attorneys and Agents who desire to submit prior art for consideration by the U.S. Patent and Trademark Office. It is respectfully pointed out that Applicant's argument that "conventional" art is not "prior" art is not persuasive and possibly improper in view of the Ueda.

(13) It is respectfully pointed out that layers are lined up per Ueda, Figure 15F, above.

(14) It is respectfully pointed out that in so far as Applicant has not argued rejection(s) of the limitations of dependent claim(s), Applicant has acquiesced said rejection(s).

Examiner has made every effort to afford due diligence in addressing all of Applicant's substantive arguments.

Any references cited but not applied are relevant to the instant Application.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Timothy L. Rude whose telephone number is (571) 272-2301. The examiner can normally be reached on Mon-Thurs.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David C. Nelms can be reached on (571) 272-1787. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Art Unit: 2871

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.



tlr

Timothy L Rude
Examiner
Art Unit 2871



3/4/07